



SGM44601

4Ω, High Speed, Low Voltage Dual, DPDT Analog Switch

GENERAL DESCRIPTION

The SGM44601 is a high-speed, low-voltage, advanced dual-independent double-pole/double-throw (DPDT) CMOS analog switch that is designed to operate from a single +1.8V to +5.5V power supply. It features high-bandwidth (300MHz) and low on-resistance (4Ω TYP), targeted applications for audio switching.

The SGM44601 is configured as a dual double-pole /double-throw (DPDT) device with two logic control inputs that control two multiplexer/demultiplexers each. The configuration can also be used as a dual differential 2-to-1 multiplexer/ demultiplexer.

SGM44601 is available in Pb-free TQFN-16 (2.6mm × 1.8mm) package.

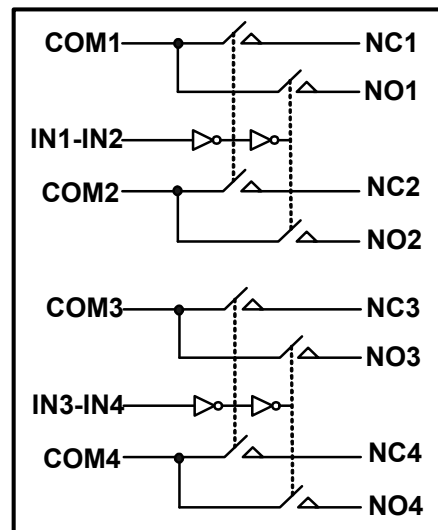
APPLICATIONS

Communication Systems
Cell Phones
Portable Instrumentation
Audio Signal Routing
Audio and Video Switching
PCMCIA Cards
Computer Peripherals
Modems
PDAs

FEATURES

- Low Voltage Operation: 1.8V to 5.5V
- Low On-Resistance: 4Ω (TYP)
- Low On-Resistance Flatness
- -3dB Bandwidth: 300MHz
- Rail-to-Rail Input and Output Operation
- High Off-Isolation: -75dB at 1MHz
- Low Crosstalk: -100dB at 1MHz
- Typical Power Consumption (<0.01μW)
- TTL/CMOS Compatible
- Lead (Pb) Free TQFN-16 (2.6mm × 1.8mm) Package
- Extended Industrial Temperature Range:
-40°C to +85°C

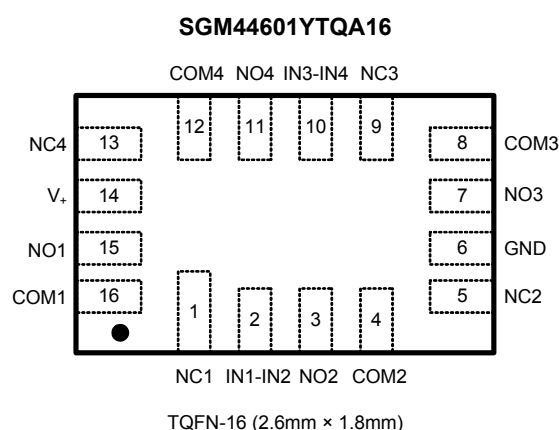
BLOCK DIAGRAM



ORDERING INFORMATION

MODEL	PIN-PACKAGE	SPECIFIED TEMPERATURE RANGE	ORDERING NUMBER	PACKAGE MARKING	PACKAGE OPTION
SGM44601	TQFN-16 (2.6mm×1.8mm)	-40°C to +85°C	SGM44601YTQA16/TR	44601	Tape and Reel, 3000

PIN CONFIGURATION (TOP VIEW)



ABSOLUTE MAXIMUM RATINGS

V_+ to GND.....0V to 6V
 Analog, Digital voltage range..... -0.3V to (V_+) +0.3V
 Continuous Current NO, NC, or COM±100mA
 Operating Temperature Range.....-40°C to +85°C
 Junction Temperature.....150°C
 Storage Temperature..... -65°C to +150°C
 Lead Temperature (soldering, 10s).....260°C

Stresses beyond those listed under “Absolute Maximum Ratings” may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

FUNCTION TABLE

IN1-IN2	Function	
	NC1 and NC2	NO1 and NO2
0	ON	OFF
1	OFF	ON

IN3-IN4	Function	
	NC3 and NC4	NO3 and NO4
0	ON	OFF
1	OFF	ON

PIN DESCRIPTION

NAME	TQFN PIN	FUNCTION
V_+	14	Power supply
GND	6	Ground
IN_x	2, 10	Digital control pin to connect the COM terminal to the NO or NC terminals
COM_x	16, 4, 8, 12	Common terminal
NO_x	15, 3, 7, 11	Normally-open terminal
NC_x	1, 5, 9, 13	Normally-closed terminal

Note: NO_x , NC_x and COM_x terminals may be an input or output.

ELECTRICAL CHARACTERISTICS

($V_+ = +4.5V$ to $+5.5V$, $GND = 0V$, $V_{IH} = +1.6V$, $V_{IL} = +0.5V$, $T_A = -40^\circ C$ to $+85^\circ C$. Typical values are at $V_+ = +5.0V$, $T_A = +25^\circ C$, unless otherwise noted.)

PARAMETER	SYMBOL	CONDITIONS	TEMP	MIN	TYP	MAX	UNITS
ANALOG SWITCH							
Analog Signal Range	V_{NO}, V_{NC}, V_{COM}		$-40^\circ C$ to $+85^\circ C$	0		V_+	V
On-Resistance	R_{ON}	$V_+ = 4.5V, 0V \leq V_{NO} \text{ or } V_{NC} \leq V_+, I_{COM} = -100mA$, Test Circuit 1	$+25^\circ C$		4	6	Ω
			$-40^\circ C$ to $+85^\circ C$			7	Ω
On-Resistance Match Between Channels	ΔR_{ON}	$V_+ = 4.5V, 0V \leq V_{NO} \text{ or } V_{NC} \leq V_+, I_{COM} = -100mA$, Test Circuit 1	$+25^\circ C$		0.4	2.5	Ω
			$-40^\circ C$ to $+85^\circ C$			3	Ω
On-Resistance Flatness	$R_{FLAT(ON)}$	$V_+ = 4.5V, 0V \leq V_{NO} \text{ or } V_{NC} \leq V_+, I_{COM} = -100mA$, Test Circuit 1	$+25^\circ C$		2	3	Ω
			$-40^\circ C$ to $+85^\circ C$			3.5	Ω
Source OFF Leakage Current	$I_{NC(OFF)}, I_{NO(OFF)}$	$V_+ = 5.5V, V_{NO} \text{ or } V_{NC} = 3.3V/0.3V, V_{COM} = 0.3V/3.3V$	$-40^\circ C$ to $+85^\circ C$			1	μA
Channel ON Leakage Current	$I_{NC(ON)}, I_{NO(ON)}, I_{COM(ON)}$	$V_+ = 5.5V, V_{COM} = 0.3V/3.3V, V_{NO} \text{ or } V_{NC} = 0.3V/3.3V$, or floating	$-40^\circ C$ to $+85^\circ C$			1	μA
DIGITAL INPUTS							
Input High Voltage	V_{INH}		$-40^\circ C$ to $+85^\circ C$	1.6			V
Input Low Voltage	V_{INL}		$-40^\circ C$ to $+85^\circ C$			0.5	V
Input Leakage Current	I_{IN}	$V_+ = 5.5V, V_{IN} = 0V \text{ or } 5.5V$	$-40^\circ C$ to $+85^\circ C$			1	μA
DYNAMIC CHARACTERISTICS							
Turn-On Time	t_{ON}	$V_{NC} \text{ or } V_{NO} = 3.0V, R_L = 300\Omega, C_L = 35pF$, Test Circuit2	$+25^\circ C$		36		ns
Turn-Off Time	t_{OFF}		$+25^\circ C$		30		ns
Break-Before-Make Time Delay	t_D	$V_{NC} \text{ or } V_{NO} = 3.0V, R_L = 300\Omega, C_L = 35pF$, Test Circuit4	$+25^\circ C$		16		ns
Charge Injection	Q	$V_G = GND, R_G = 0\Omega, C_L = 1.0nF, Q = C_L \times V_{OUT}$, Test Circuit3	$+25^\circ C$		3.5		pC
Off Isolation	O_{ISO}	Signal = 0dBm, $R_L = 50\Omega$, Test Circuit5	1MHz	$+25^\circ C$		-75	dB
			10MHz	$+25^\circ C$		-55	
Channel-to-Channel Crosstalk	X_{TALK}	Signal = 0dBm, $R_L = 50\Omega$, Test Circuit6	1MHz	$+25^\circ C$		-100	dB
			10MHz	$+25^\circ C$		-60	
-3dB Bandwidth	BW	Signal = 0dBm, $R_L = 50\Omega$, Test Circuit7	$+25^\circ C$		300		MHz
Channel ON Capacitance	$C_{NC(ON)}, C_{NO(ON)}, C_{COM(ON)}$		$+25^\circ C$		43.2		pF
POWER REQUIREMENTS							
Power Supply Range	V_+		$-40^\circ C$ to $+85^\circ C$	1.8		5.5	V
Power Supply Current	I_+	$V_+ = 5.5V, V_{IN} = 0V \text{ or } V_+$	$-40^\circ C$ to $+85^\circ C$			1	μA

Specifications subject to changes without notice.

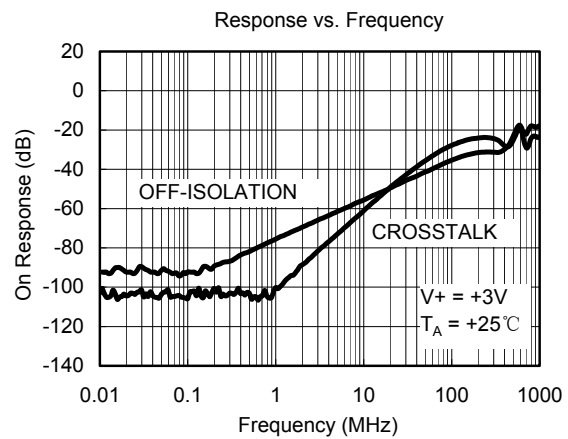
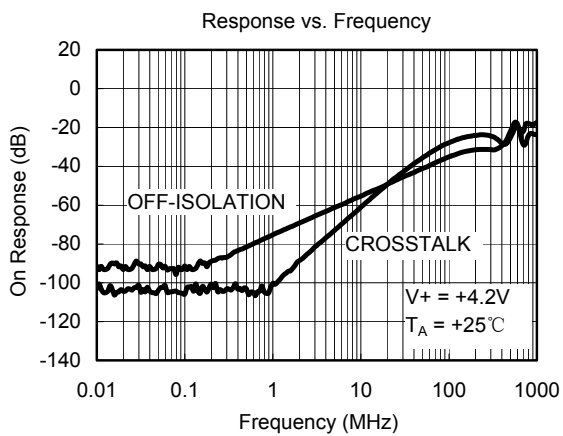
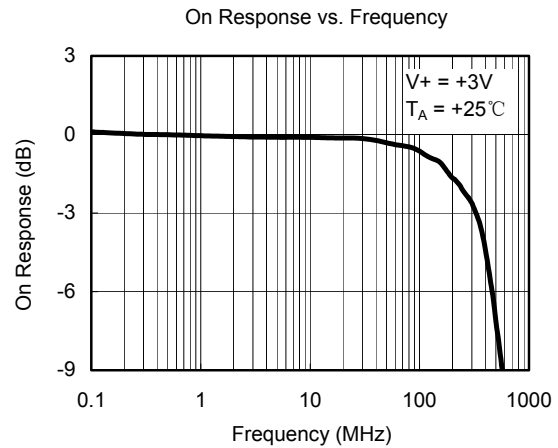
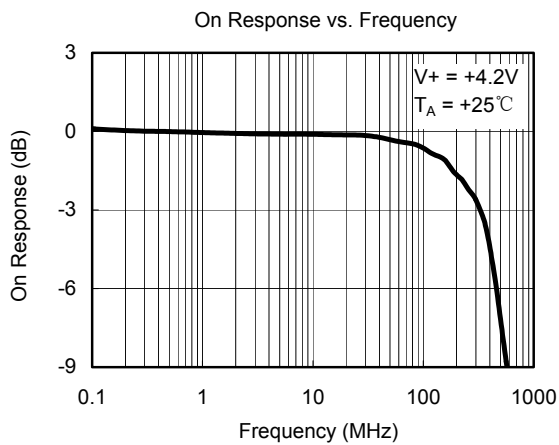
ELECTRICAL CHARACTERISTICS

($V_+ = +2.7V$ to $+3.6V$, $V_{IH} = +1.6V$, $V_{IL} = +0.4V$, $T_A = -40^\circ C$ to $+85^\circ C$. Typical values are at $V_+ = +3.0V$, $T_A = +25^\circ C$, unless otherwise noted.)

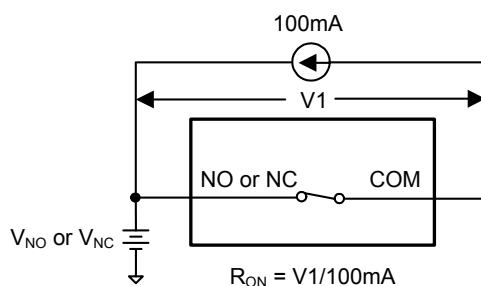
PARAMETER	SYMBOL	CONDITIONS	TEMP	MIN	TYP	MAX	UNITS
ANALOG SWITCH							
Analog Signal Range	V_{NO}, V_{NC}, V_{COM}		$-40^\circ C$ to $+85^\circ C$	0		V_+	V
On-Resistance	R_{ON}	$V_+ = 2.7V, 0V \leq V_{NO} \text{ or } V_{NC} \leq V_+, I_{COM} = -100mA$, Test Circuit 1	$+25^\circ C$		10	15	Ω
			$-40^\circ C$ to $+85^\circ C$			18	Ω
On-Resistance Match Between Channels	ΔR_{ON}	$V_+ = 2.7V, 0V \leq V_{NO} \text{ or } V_{NC} \leq V_+, I_{COM} = -100mA$, Test Circuit 1	$+25^\circ C$		1	3	Ω
			$-40^\circ C$ to $+85^\circ C$			4	Ω
On-Resistance Flatness	$R_{FLAT(ON)}$	$V_+ = 2.7V, 0V \leq V_{NO} \text{ or } V_{NC} \leq V_+, I_{COM} = -100mA$, Test Circuit 1	$+25^\circ C$		6	9	Ω
			$-40^\circ C$ to $+85^\circ C$			12	Ω
Source OFF Leakage Current	$I_{NC(OFF)}, I_{NO(OFF)}$	$V_+ = 3.6V, V_{NO} \text{ or } V_{NC} = 3.3V / 0.3V, V_{COM} = 0.3V / 3.3V$	$-40^\circ C$ to $+85^\circ C$			1	μA
Channel ON Leakage Current	$I_{NC(ON)}, I_{NO(ON)}, I_{COM(ON)}$	$V_+ = 3.6V, V_{COM} = 0.3V / 3.3V, V_{NO} \text{ or } V_{NC} = 0.3V / 3.3V$, or floating	$-40^\circ C$ to $+85^\circ C$			1	μA
DIGITAL INPUTS							
Input High Voltage	V_{INH}		$-40^\circ C$ to $+85^\circ C$	1.5			V
Input Low Voltage	V_{INL}		$-40^\circ C$ to $+85^\circ C$			0.4	V
Input Leakage Current	I_{IN}	$V_+ = 2.7V, V_{IN} = 0V \text{ or } 2.7V$	$-40^\circ C$ to $+85^\circ C$			1	μA
DYNAMIC CHARACTERISTICS							
Turn-On Time	t_{ON}	$V_{NC} \text{ or } V_{NO} = 1.5V, R_L = 300\Omega, C_L = 35pF$, Test Circuit2	$+25^\circ C$		45		ns
Turn-Off Time	t_{OFF}		$+25^\circ C$		44		ns
Break-Before-Make Time Delay	t_D	$V_{NC} \text{ or } V_{NO} = 1.5V, R_L = 300\Omega, C_L = 35pF$, Test Circuit4	$+25^\circ C$		23		ns
Charge Injection	Q	$V_G = GND, R_G = 0\Omega, C_L = 1.0nF, Q = C_L \times V_{OUT}$, Test Circuit3	$+25^\circ C$		2.6		pC
Off Isolation	O_{ISO}	Signal = 0dBm, $R_L = 50\Omega$, Test Circuit5	1MHz	$+25^\circ C$		-75	dB
			10MHz	$+25^\circ C$		-55	dB
Channel-to-Channel Crosstalk	X_{TALK}	Signal = 0dBm, $R_L = 50\Omega$, Test Circuit6	1MHz	$+25^\circ C$		-100	dB
			10MHz	$+25^\circ C$		-60	dB
-3dB Bandwidth	BW	Signal = 0dBm, $R_L = 50\Omega$, Test Circuit7	$+25^\circ C$		300		MHz
Channel ON Capacitance	$C_{NC(ON)}, C_{NO(ON)}, C_{COM(ON)}$		$+25^\circ C$		43.2		pF

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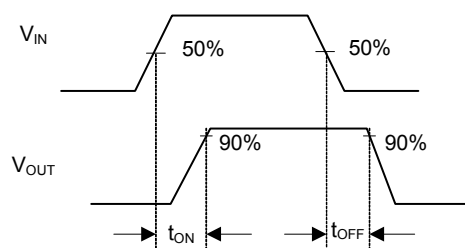
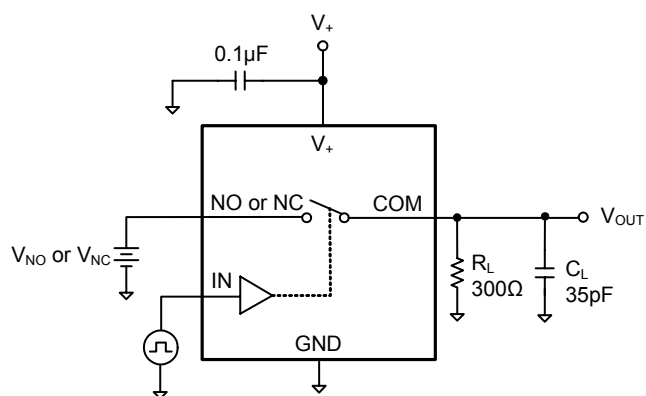
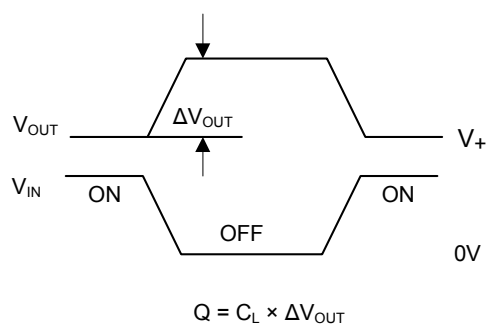
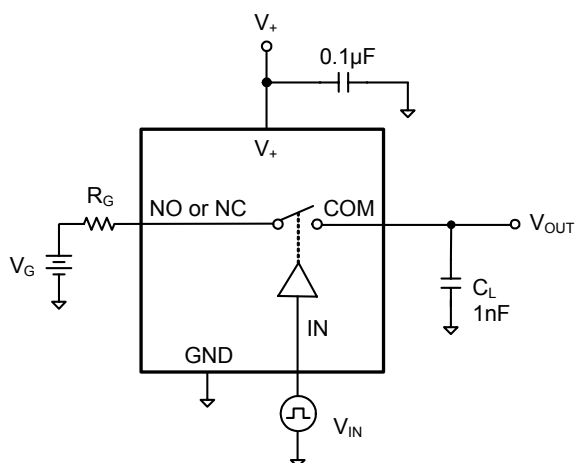
TYPICAL PERFORMANCE CHARACTERISTICS



TEST CIRCUITS

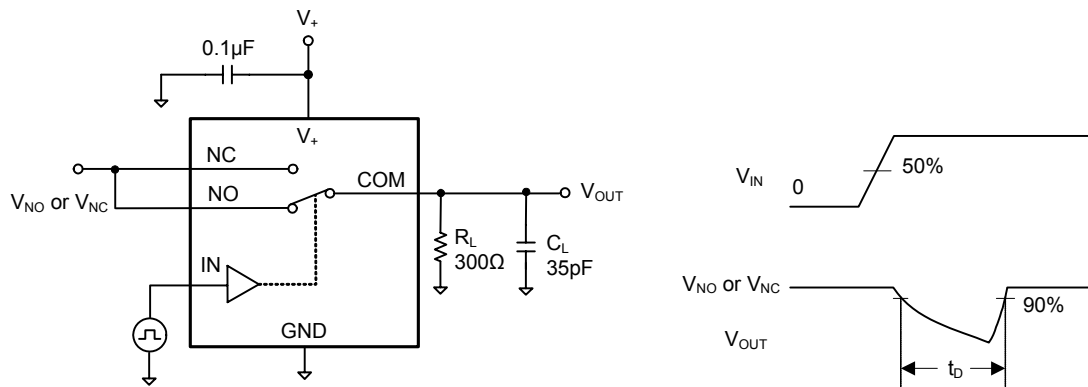
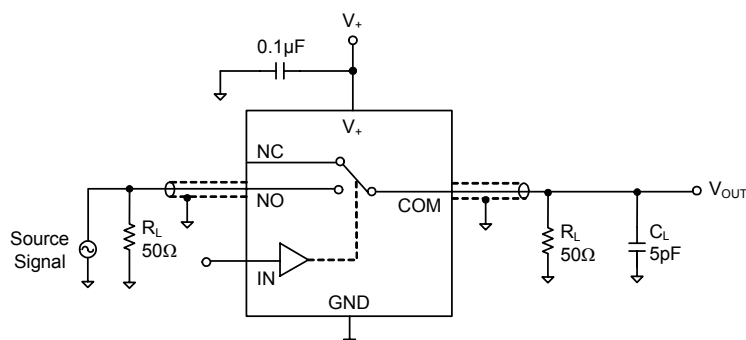


Test Circuit 1. On Resistance

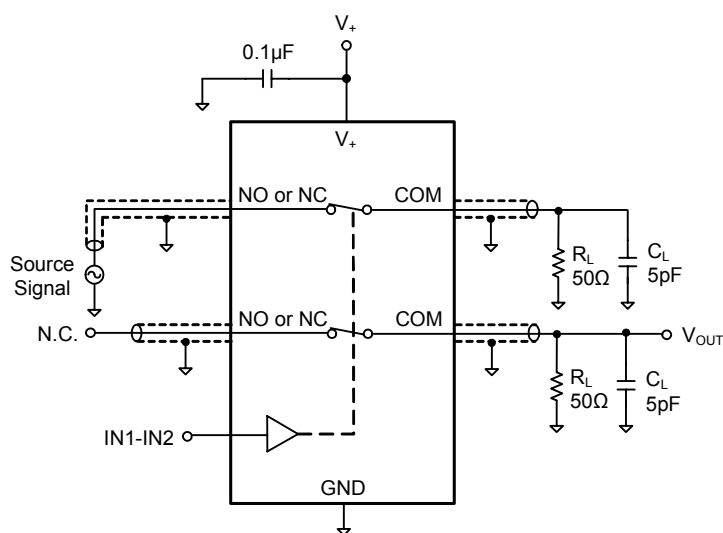
Test Circuit 2. Switching Times (t_{ON} , t_{OFF})

Test Circuit 3. Charge Injection

TEST CIRCUITS (Cont.)

Test Circuit 4. Break-Before-Make Time Delay (t_b)

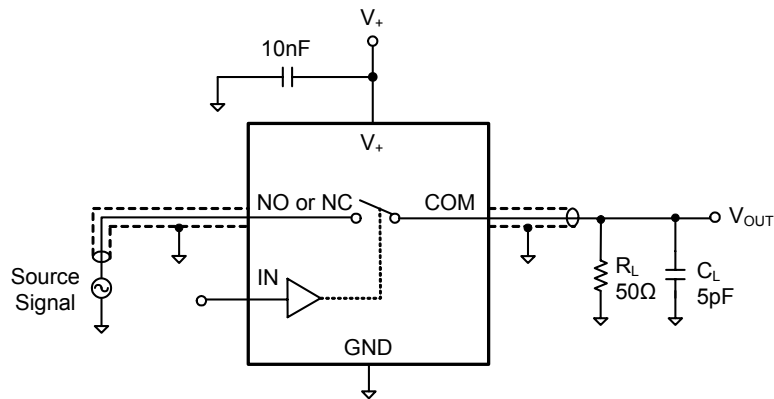
Test Circuit 5. Off Isolation



$$\text{Channel To Channel Crosstalk} = -20 \times \log \frac{V_{NO \text{ or } V_{NC}}}{V_{OUT}}$$

Test Circuit 6. Channel-to-Channel Crosstalk

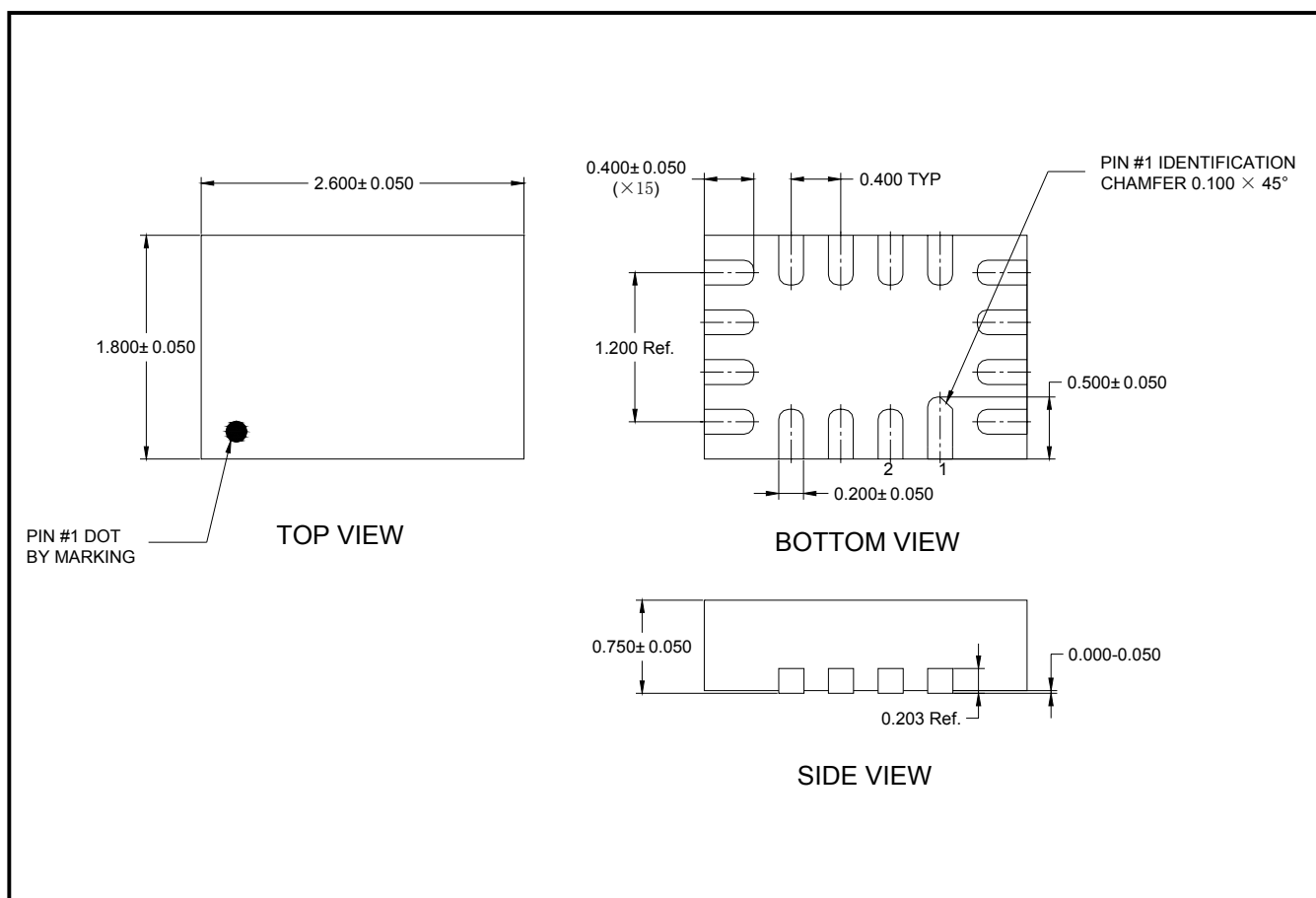
TEST CIRCUITS (Cont.)



Test Circuit 7. -3dB Bandwidth

PACKAGE OUTLINE DIMENSIONS

TQFN-16 (2.6mm × 1.8mm)



Note: All linear dimensions are in millimeters.

12/2008 REV. A. 1

SGMICRO is dedicated to provide high quality and high performance analog IC products to customers. All SGMICRO products meet the highest industry standards with strict and comprehensive test and quality control systems to achieve world-class consistency and reliability.

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